### TABLE I continued

Water-powder ratio	Control	Impregnated	Strength factor
0.50	0.74	2.78	3.75
0.60	0.67	2.98	4.45
0.70	0.40	2.75	6.88
0.80	0.32	1.41	4.40

(e) Abrasion resistance % weight loss						
Water-powder ratio	Control	Impregnated	Strength factor			
0.50	6.4	0.9	7.1			
0.60	8.6	1.1	7.8			
0.70	9.2	1.7	5.4			
0.80	9.3	1.9	4.9			
(f) Polymer load	ings					
Water-powder ratio		% Polymer absorbed				
0.50		21.9	······			
0.60		28.3				
0.70		35.4				
0.80		41.7				

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5.4
4.9
ymer absorbed
<u></u>

## Correlations between oxygen transport phenomena in non-crystalline silica

The mobility of oxygen in fused silica is evident in a variety of phenomena such as permeation of  $O_2$ gas, oxidation of silicon surfaces, and  $O_2/SiO_2$ isotope exchange. However, a mechanistic relationship between all these processes has not yet been presented. The formation of amorphous silica scales during oxidation of silicon is known to be rate-controlled by permeation of molecular  $O_2$ through the  $SiO_2$  layer [1]. On the other hand, oxygen tracer diffusion coefficients as measured by isotopic exchange techniques are said to be uncorrelated to O<sub>2</sub> diffusion-controlled phenomena [2]. However, there should be a common underlying mechanism for the transport of oxygen because all the processes have uniformly low activation energies, depend linearly on the partial pressure of oxygen  $(p_{O_1})$ , as well as having algebraic relationships between their respective rate laws. All these observations can be understood if the transport of oxygen involves the interaction of  $O_2$  molecules dissolved in SiO<sub>2</sub> with oxygen of the silica network (lattice oxygen).

Haul and Dümbgen [3] were the first to relate permeability of  $O_2$  gas to diffusion coefficients measured by gas/solid isotope exchange. In their model interstitially dissolved  $O_2$  acts as a defect by which lattice oxygen migrates. The diffusion of lattice oxygen  $(D_0)$  then, can be related to  $O_2$  permeability  $(P_{O_2})$ ,

by

$$P_{O_2} = D_{O_2} c_{O_2} / 7.6 \tag{1}$$

$$D_{\rm O} = D_{\rm O_2} c_{\rm O_2} / c_{\rm O} = 7.6 P_{\rm O_2} / c_{\rm O}$$
 (2)

where  $P_{O_2}$  is in units of cm<sup>3</sup> gas (STP) sec<sup>-1</sup> for a 1 mm thick wall, 1 cm<sup>2</sup> area at 10 Torr gas pressure difference;  $D_{O_2}$  is the diffusion coefficient of molecular oxygen in cm<sup>2</sup> sec<sup>-1</sup>;  $c_{O_2}$  and  $c_O$  are the concentrations of oxygen in units of cm<sup>3</sup> gas (STP) per cm<sup>3</sup> solid for dissolved O<sub>2</sub> and lattice oxygen in SiO<sub>2</sub> respectively.

The oxidation rate of silicon to silica (parabolic regime) is correlated with  $O_2$  permeability [4], because the oxidation proceeds by diffusion of dissolved  $O_2$  through the SiO<sub>2</sub> layer to the SiO<sub>2</sub>/Si interface. Dankwerts [5] has shown that parabolic oxidation of surfaces can be described by a rate constant:

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$\overline{D_{\mathbf{O}}, k_{\mathbf{O}} (\mathrm{cm}^2 \mathrm{sec}^{-1})}$	Q (kcal mol <sup>-1</sup> )	Т (°С)	Pressure dependence	Reference
<sup>18</sup> O-tracer diffusion ( $D_O$	.)			
$2.0 \times 10^{-9}$ (4.4 ± <sup>14</sup> <sub>3</sub> ) × 10 <sup>-11</sup>	29.0 ± 2.0 ± 2.0 19.7 ± 4.0	850-1250 1150-1430	$D_{O} \propto p_{O_2}$	[6] [7]
$O_2$ permeation ( $P_{O_2}$ )				
	31.4 22.0*	840-940 900-1100	$\overline{P}_{\mathbf{O}_2} \propto p_{\mathbf{O}_2}$	[8] [9]
$O_2$ diffusion ( $D_{O_2}$ )				
$2.8 \times 10^{-4}$ <sup>†</sup>	27.0	900-1100		[10]
Parabolic rate constant f	or oxidation of silicon in O	$_{2}(k_{\rm SiO_{2}})$		
2.0 × 10 <sup>-9</sup> ‡ 2.0 × 10 <sup>-9</sup>	28.5 31.0	8001200 9001150	$k_{SiO_2} \propto p_{O_2}$ $k_{SiO_2} \propto p_{O_2}$ flow system	[1] [11]
$1.0  imes 10^{-10}$	23.0	950-1100	$k_{SiO_2} \propto p_{O_2}$ manostatic	[11]
$1.2 \times 10^{-9}$	27.6	900-1300	_ r.f. heating	[12]
1.1 × 10 <sup>-9</sup>	28.0	900-1250	– resistance heating	[12]

TABLE I Comparison between  $^{18}$  O-tracer diffusion, oxygen permeation, oxygen diffusion in SiO  $_2\,$  glass, and oxidation of silicon

 $D_{\mathbf{O}}, k_{\mathbf{O}} \stackrel{\circ}{=} \text{pre-exponential factor}, Q \stackrel{\circ}{=} \text{activation energy}$ 

\*Revised value 27 kcal mol<sup>-1</sup> [10].

<sup>†</sup>Calculated from data given in [10].

‡Calculated from data given in [1].

$$k_{\rm SiO_2} = 2D_{\rm O_2} c_{\rm O_2} / c_{\rm O}, \qquad (3)$$

provided that the solubility of  $O_2$  is sufficiently small, i.e.  $c_{O_2} \ll c_{O^*}$ ;  $k_{SiO_2}$  is in units of cm<sup>2</sup> sec<sup>-1</sup>.

Equations 1 to 3 show clearly that  $D_0$ ,  $D_{O_2}$ ,  $P_{O_2}$  and  $k_{SiO_2}$  are all interdependent and that the equations can be rearranged. For instance,  $P_{O_2}$  and  $k_{SiO_2}$  are solely dependent on tracer oxygen diffusivity  $(D_0)$  in SiO<sub>2</sub>.

$$P_{0_{\gamma}} = c_0 D_0 / 7.6 \tag{4}$$

$$k_{\rm SiO_2} = 2D_0 \tag{5}$$

Thus tracer diffusion studies are in fact more useful in elucidating oxygen transport processes than was stated by Meek [2].

It follows from Equations 4 and 5 that  $P_{O_2}$ ,  $k_{SiO_2}$ , and  $D_O$  should have the same temperature dependence.  $D_{O_2}$  is expected to have that same temperature dependence (see Equation 2) but reduced by the heat of solution of  $O_2$  in SiO<sub>2</sub>,

which, however, is small [10]. Table I lists data from the literature which show that the four rates do have the same low activation energies (20 to 30 kcal mol<sup>-1</sup>) within experimental error. Not included in Table I are experiments which show higher activation energies of 71 [13] and  $55 \text{ kcal mol}^{-1}$  [3] for tracer diffusion because they were influenced by phase-boundary reactions [6, 7]. Table I also shows that oxygen transport in SiO<sub>2</sub> is directly proportional to  $p_{O_2}$ , in marked contrast to the  $p_{O_2}^{-1/2}$  dependence found for oxygen diffusion in  $K_2O-SiO_2$  glasses [14]. The mechanism of oxygen transport must therefore differ when network-modifying cations are present in the  $SiO_2$  network. Diffusion in the multicomponent silicates occurs not via interstitially dissolved  $O_2$  molecules as in pure SiO<sub>2</sub>, but via oxygen vacancies [14]. The activation energies of oxygen diffusion in silicate glasses [14] are much higher than that of SiO<sub>2</sub> glass because diffusion by oxygen vacancies requires the

 $<sup>{}^{*}</sup>c_{O_{2}}$  (900 to 1100° C) = (1.7 to 2) × 10<sup>-3</sup> cm<sup>3</sup> gas (STP) per cm<sup>3</sup> SiO<sub>2</sub> [10]  $c_{O} = 821$  cm<sup>3</sup> gas (STP) per cm<sup>3</sup> SiO<sub>2</sub>, i.e.  $c_{O_{2}}/c_{O} = 2.1 \times 10^{-6}$ 

breaking of Si–O bonds. The outlined diffusion mechanism in SiO<sub>2</sub> also seems to hold for high temperature (1100 to  $1500^{\circ}$  C) corrosion of SiC and Si<sub>3</sub>N<sub>4</sub> during which SiO<sub>2</sub> layers form. Activation energies of 20 to 30 kcal mol<sup>-1</sup> were observed in the oxidation (parabolic regime) of SiC [15, 16] and around 25 to 35 kcal mol<sup>-1</sup> for pure Si<sub>3</sub>N<sub>4</sub> [17, 18]. The activation energy for the oxidation of impure Si<sub>3</sub>N<sub>4</sub> increases with impurity content [19]. Instead of pure SiO<sub>2</sub>, the impure Si<sub>3</sub>N<sub>4</sub> forms silicate glass layers that presumably have higher activation energies of tracer oxygen diffusion.

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# Kinetics of solid state $NiFe_2O_4$ formation at 700 to 1400° C

Ferrites are fabricated by heating powders, and many processing variables, e.g. powder purity, size distribution, type, etc., effect the reaction rate [1]. Activation energies for NiO + Fe<sub>2</sub>O<sub>3</sub> = NiFe<sub>2</sub>O<sub>4</sub> have varied from 105 and 185 kJ mol<sup>-1</sup> [2] and 225 to 293 kJ mol<sup>-1</sup> [3]. In the present work spectrographically pure (J. Matthey) NiO and Fe<sub>2</sub>O<sub>3</sub> with sieved particle sizes of 15.6 to 33.0  $\mu$ m were used. Equimolar amounts were mixed by hand for over 1 h, pressed in a steel die without binder or lubrication to form a pellet 10 mm diameter and 4 mm thick, placed in a recrystallized alumina boat, and fired in air within a temperature variation of  $\pm 3^{\circ}$  C. The amount of

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NiFe<sub>2</sub>O<sub>4</sub> formed was measured by the force in a magnetic field. Chamfered pole pieces of an electromagnet gave a region of constant field gradient and a double pan chemical balance was used to measure the force. A phosphor bronze cantilever was used to prevent the specimen being attracted to either pole. Its stiffness could be neglected during weighing when the specimen returned (checked by a cathetometer) to a null position. A Cu specimen holder was used to hold about 100 mg powdered sample. The force per unit mass of sample versus mol% NiFe<sub>2</sub>O<sub>4</sub> in a range of NiO, Fe<sub>2</sub>O<sub>3</sub> and NiFe<sub>2</sub>O<sub>4</sub> mixtures was linear and used to determine the unknown amount of NiFe<sub>2</sub>O<sub>4</sub> in a sample.

Compacting pressures in the range 10 to 100 MPa did not affect the amount of  $NiFe_2O_4$  © 1978 Chapman and Hall Ltd. Printed in Great Britain.